

June 2014

# FDA16N50\_F109

# N-Channel UniFET<sup>TM</sup> MOSFET

**500V**, **16.5 A**, **380** mΩ

### **Features**

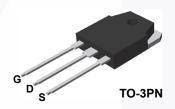
- $R_{DS(on)}$  = 380  $m\Omega$  (Max.) @  $V_{GS}$  = 10,  $I_D$  = 8.3 A
- Low Gate Charge (Typ. 32 nC)
- Low C<sub>rss</sub> (Typ. 20 pF)
- · 100% Avalanche Tested

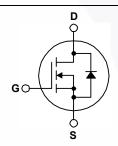
## **Applications**

- PDP TV
- · Uninterruptible Power Supply

## **Description**

UniFET<sup>TM</sup> MOSFET is Fairchild Semiconductor's high voltage MOSFET family based on planar stripe and DMOS technology. This MOSFET is tailored to reduce on-state resistance, and to provide better switching performance and higher avalanche energy strength. This device family is suitable for switching power converter applications such as power factor correction (PFC), flat panel display (FPD) TV power, ATX and electronic lamp ballasts.





## **Absolute Maximum Ratings** T<sub>C</sub> = 25°C unless otherwise noted.

Symbol		Parameter		FDA16N50_F109	Unit	
V <sub>DSS</sub>	Drain-Source Voltage			500	V	
I <sub>D</sub>	Drain Current	urrent - Continuous ( $T_C = 25^{\circ}C$ ) 16.5 - Continuous ( $T_C = 100^{\circ}C$ ) 9.9			A A	
I <sub>DM</sub>	Drain Current	- Pulsed	(Note 1)	66	Α	
V <sub>GSS</sub>	Gate-Source voltage			±30	V	
E <sub>AS</sub>	Single Pulsed Avalanche Energy		(Note 2)	780	mJ	
I <sub>AR</sub>	Avalanche Current		(Note 1)	16.5	А	
E <sub>AR</sub>	Repetitive Avalanche Energy		(Note 1)	20.5	mJ	
dv/dt	Peak Diode Recovery dv/dt (N		(Note 3)	4.5	V/ns	
P <sub>D</sub>	Power Dissipation	(T <sub>C</sub> = 25°C) - Derate above 25°C		205 2.1	W W/°C	
T <sub>J,</sub> T <sub>STG</sub>	Operating and Storage Temperature Range			-55 to +150	°C	
T <sub>L</sub>	Maximum Lead Temperature for Soldering Purpose, 1/8" from Case for 5 Seconds		ose,	300	°C	

### **Thermal Characteristics**

Symbol	Parameter	FDA16N50_F109	Unit	
$R_{\theta JC}$	nermal Resistance, Junction-to-Case, Max. 0.6		°C/W	
$R_{\theta JA}$	Thermal Resistance, Junction-to-Ambient, Max.	40	C/VV	

## **Package Marking and Ordering Information**

<b>Device Marking</b>	Device	Package	Reel Size	Tape Width	Quantity
FDA16N50	FDA16N50_F109	TO-3PN	Tube	N/A	30 units

# **Electrical Characteristics** $T_C = 25$ °C unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Тур.	Max	Unit
Off Charac	teristics			ı		
BV <sub>DSS</sub>	Drain-Source Breakdown Voltage	V <sub>GS</sub> = 0V, I <sub>D</sub> = 250μA	500			V
ΔBV <sub>DSS</sub> / ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	I <sub>D</sub> = 250μA, Referenced to 25°C		0.5		V/°C
I <sub>DSS</sub>	Zero Gate Voltage Drain Current	V <sub>DS</sub> = 500V, V <sub>GS</sub> = 0V V <sub>DS</sub> = 400V, T <sub>C</sub> = 125°C			1 10	μ <b>Α</b> μ <b>Α</b>
I <sub>GSSF</sub>	Gate-Body Leakage Current, Forward	V <sub>GS</sub> = 30V, V <sub>DS</sub> = 0V			100	nA
I <sub>GSSR</sub>	Gate-Body Leakage Current, Reverse $V_{GS} = -30V$ , $V_{DS} = 0V$		-		-100	nA
On Charac	teristics					
V <sub>GS(th)</sub>	Gate Threshold Voltage	$V_{DS} = V_{GS}, I_{D} = 250 \mu A$	3.0		5.0	V
R <sub>DS(on)</sub>	Static Drain-Source On-Resistance	V <sub>GS</sub> = 10V, I <sub>D</sub> = 8.3A		0.31	0.38	Ω
g <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 40V, I <sub>D</sub> = 8.3A		23		S
Dynamic C	haracteristics			•	•	
C <sub>iss</sub>	Input Capacitance	V <sub>DS</sub> = 25V, V <sub>GS</sub> = 0V,	\	1495	1945	pF
C <sub>oss</sub>	Output Capacitance	f = 1.0MHz		235	310	pF
C <sub>rss</sub>	Reverse Transfer Capacitance			20	30	pF
Switching	Characteristics					
t <sub>d(on)</sub>	Turn-On Delay Time	V <sub>DD</sub> = 250V, I <sub>D</sub> = 16A		40	90	ns
t <sub>r</sub>	Turn-On Rise Time	$R_G = 25\Omega$	-	150	310	ns
t <sub>d(off)</sub>	Turn-Off Delay Time			65	140	ns
t <sub>f</sub>	Turn-Off Fall Time	(Note 4)		80	170	ns
Qg	Total Gate Charge	V <sub>DS</sub> = 400V, I <sub>D</sub> = 16A	/	32	45	nC
Q <sub>gs</sub>	Gate-Source Charge	V <sub>GS</sub> = 10V	-	8.5		nC
$Q_{gd}$	Gate-Drain Charge	(Note 4)		14		nC
Drain-Sour	ce Diode Characteristics and Maximur	n Ratings		I.		
I <sub>S</sub>	Maximum Continuous Drain-Source Diode Forward Current				9.2	Α
I <sub>SM</sub>	Maximum Pulsed Drain-Source Diode Forward Current				37	Α
V <sub>SD</sub>	Drain-Source Diode Forward Voltage	V <sub>GS</sub> = 0V, I <sub>S</sub> = 16.5A			1.4	V
t <sub>rr</sub>	Reverse Recovery Time	V <sub>GS</sub> = 0V, I <sub>S</sub> = 16A	-	490	-	ns
Q <sub>rr</sub>	Reverse Recovery Charge	dl <sub>F</sub> /dt =100A/μs		5.0	/	μC

#### NOTES:

<sup>1.</sup> Repetitive Rating: Pulse width limited by maximum junction temperature

<sup>2.</sup> L = 5.1mH,  $I_{AS}$  = 16.5A,  $V_{DD}$  = 50V,  $R_G$  = 25 $\Omega$ , Starting  $T_J$  = 25 $^{\circ}$ C

<sup>3.</sup>  $I_{SD} \leq$  16.5A, di/dt  $\leq$  200A/ $\mu$ s,  $V_{DD} \leq$  BV $_{DSS}$ , Starting  $T_J$  = 25°C

<sup>4.</sup> Essentially Independent of Operating Temperature Typical Characteristics

## **Typical Characteristics**

Figure 1. On-Region Characteristics

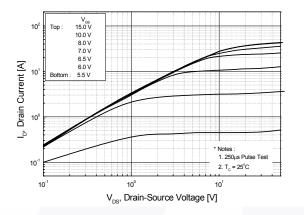


Figure 3. On-Resistance Variation vs. Drain Current and Gate Voltage

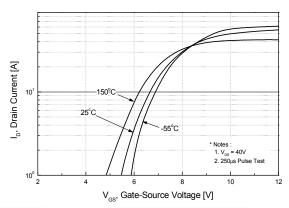


Figure 2. Transfer Characteristics

Figure 4. Body Diode Forward Voltage Variation vs. Source Current and Temperatue

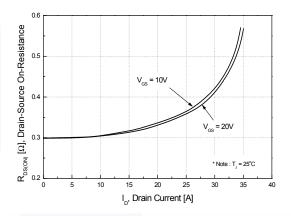
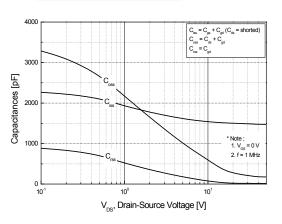


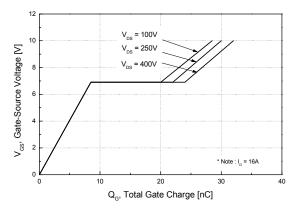
Figure 5. Capacitance Characteristics



Notes:
10°
0.2 0.4 0.6 0.8 1.0 1.2 1.4 1.6 1.8 2.0 2.2 2.4

V<sub>SD</sub>, Source-Drain voltage [V]

Figure 6. Gate Charge Characteristics



## Typical Characteristics (Continued)

Figure 7. Breakdown Voltage Variation vs. Temperature

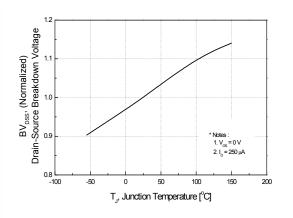


Figure 8. On-Resistance Variation vs. Temperature

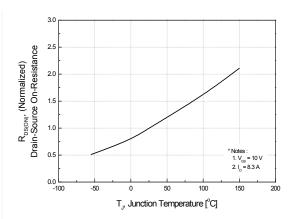
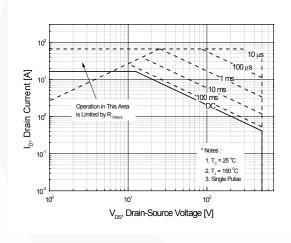


Figure 9. Maximum Safe Operating Area

Figure 10. Maximum Drain Current vs. Case Temperature



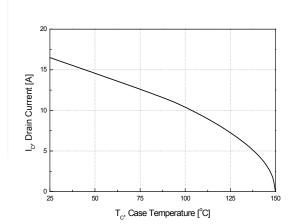


Figure 11. Transient Thermal Response Curve

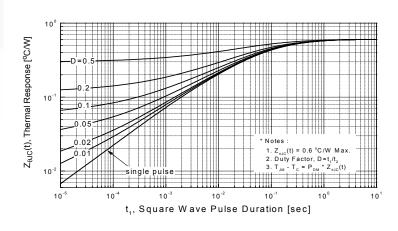


Figure 12. Gate Charge Test Circuit & Waveform

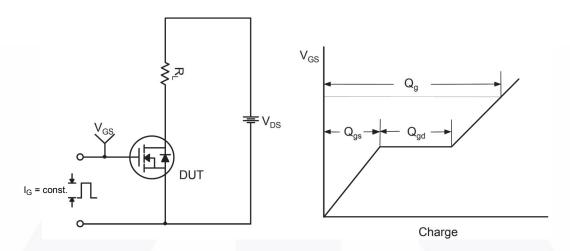


Figure 13. Resistive Switching Test Circuit & Waveforms

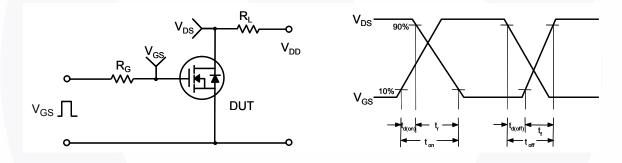
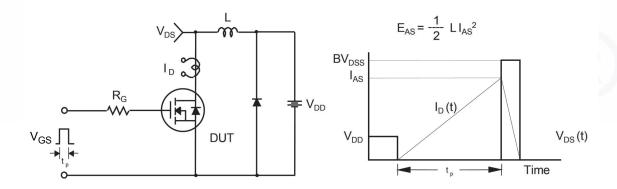


Figure 14. Unclamped Inductive Switching Test Circuit & Waveforms



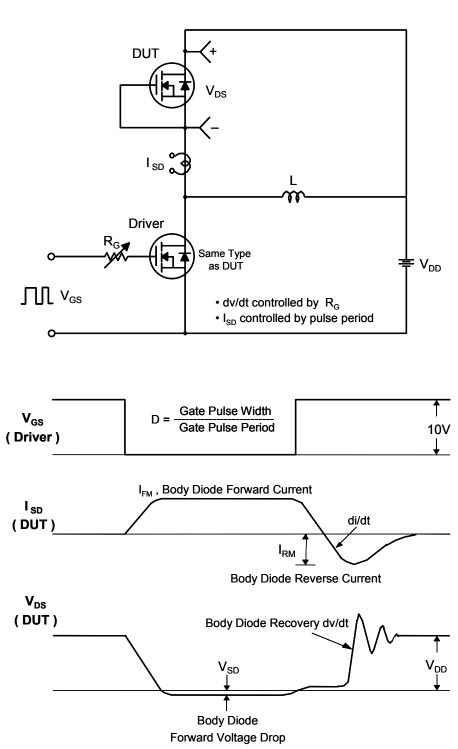
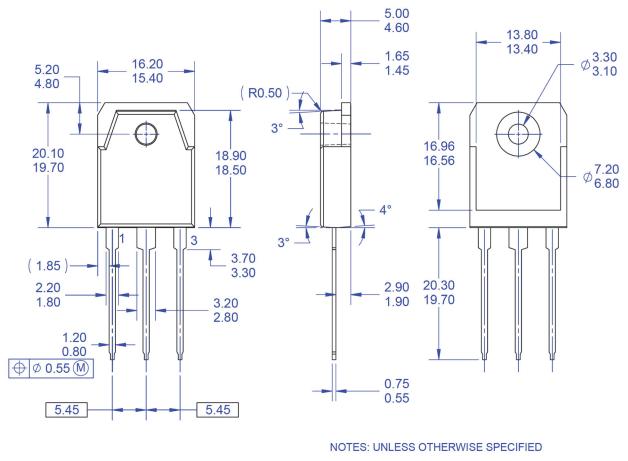
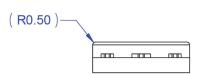


Figure 15. Peak Diode Recovery dv/dt Test Circuit & Waveforms

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- ALL DIMENSIONS ARE IN MILLIMETERS.
- **DIMENSION AND TOLERANCING PER** ASME14.5-2009.
- D) DIMENSIONS ARE EXCLUSSIVE OF BURRS, MOLD FLASH, AND TIE BAR EXTRUSSIONS.
  E) DRAWING FILE NAME: TO3PN03AREV1.
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### Figure 16. TO3PN, 3-Lead, Plastic, EIAJ SC-65

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